

ZXMP6A13F

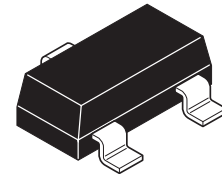
60V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = -60V$; $R_{DS(ON)} = 0.400\Omega$ $I_D = -1.1A$

DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



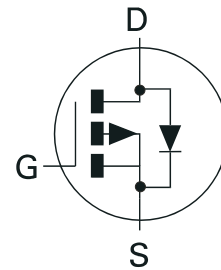
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FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

- DC - DC converters
- Power management functions
- Relay and solenoid driving
- Motor control

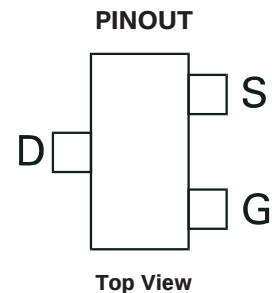


ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMP6A13FTA	7"	8mm	3000 units
ZXMP6A13FTC	13"	8mm	10000 units

DEVICE MARKING

- 7P6



Top View

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ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	-60	V
Gate Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=10V$; $T_A=25^\circ C$ ^(b) $V_{GS}=10V$; $T_A=70^\circ C$ ^(b) $V_{GS}=10V$; $T_A=25^\circ C$ ^(a)	I_D	-1.1 -0.8 -0.9	A
Pulsed Drain Current ^(c)	I_{DM}	-4.0	A
Continuous Source Current (Body Diode) ^(b)	I_S	-1.2	A
Pulsed Source Current (Body Diode) ^(c)	I_{SM}	-4.0	A
Power Dissipation at $T_A=25^\circ C$ ^(a) Linear Derating Factor	P_D	625 5	mW mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ ^(b) Linear Derating Factor	P_D	806 6.5	mW mW/ $^\circ C$
Operating and Storage Temperature Range	T_J ; T_{stg}	-55 to +150	$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient ^(a)	$R_{\theta JA}$	200	$^\circ C/W$
Junction to Ambient ^(b)	$R_{\theta JA}$	155	$^\circ C/W$

NOTES

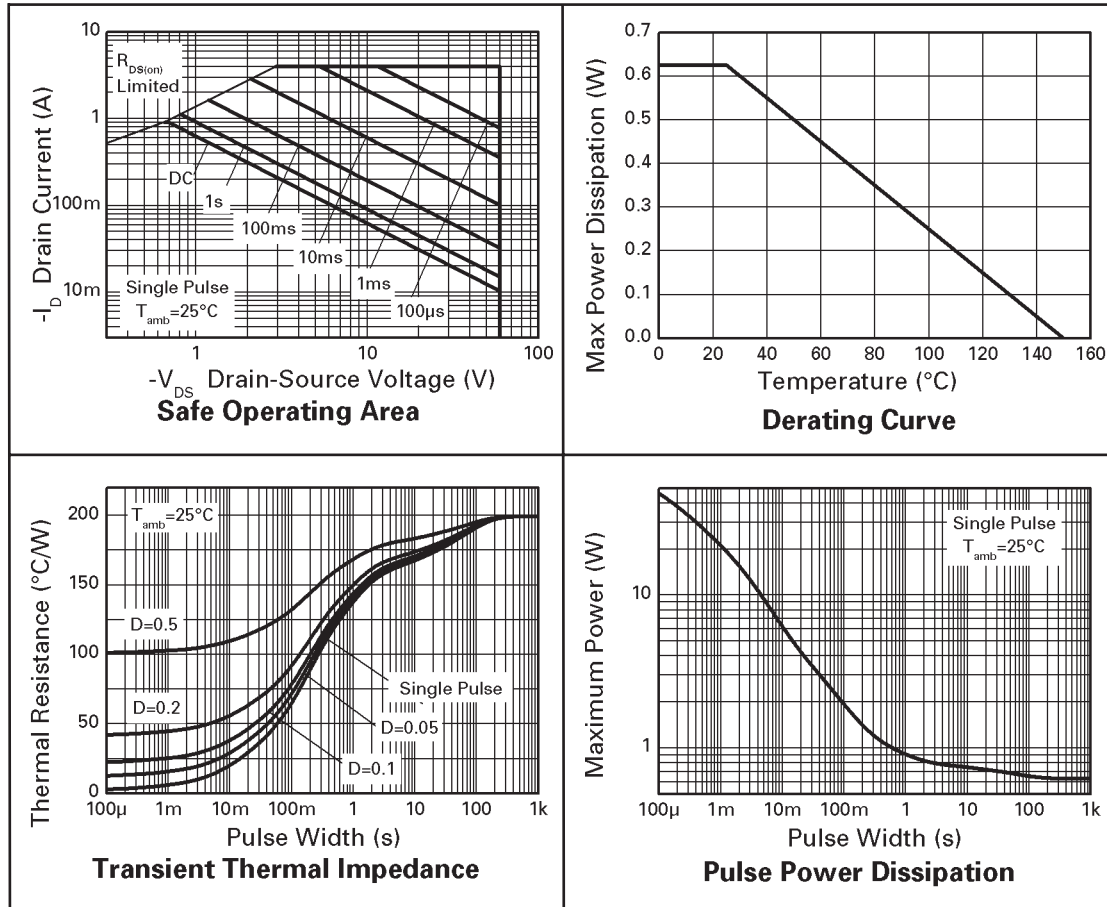
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D=0.05$ pulse width=10 μs - pulse width limited by maximum junction temperature.

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CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated)

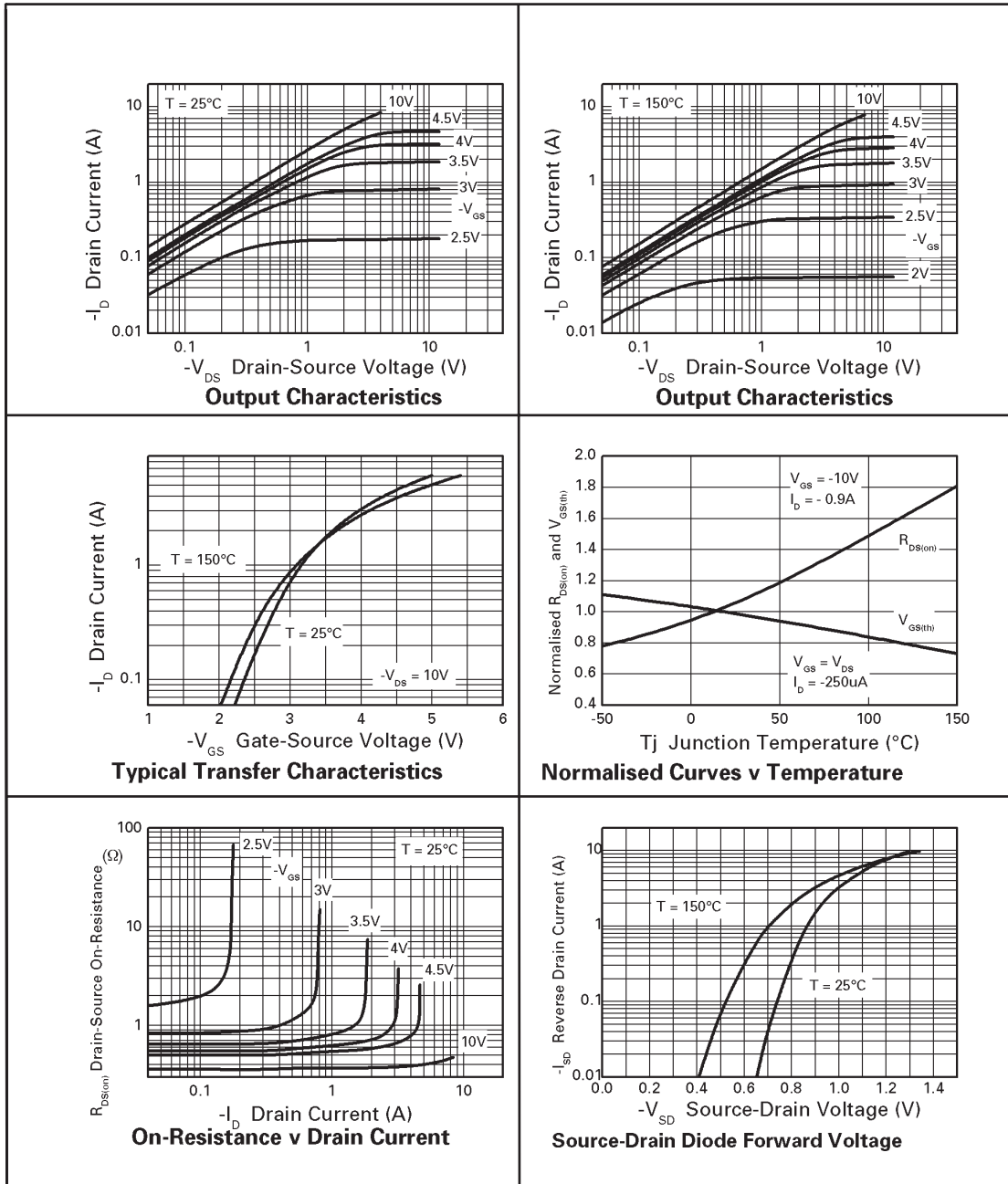
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-60			V	I _D =-250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			-1	μA	V _{DS} =-60V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	-1.0			V	I _D =-250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance ⁽¹⁾	R _{DS(on)}			0.400 0.600	Ω Ω	V _{GS} =-10V, I _D =-0.9A V _{GS} =-4.5V, I _D =-0.8A
Forward Transconductance ⁽¹⁾⁽³⁾	g _{fs}		1.8		S	V _{DS} =-15V,I _D =-0.9A
DYNAMIC ⁽³⁾						
Input Capacitance	C _{iss}		233		pF	V _{DS} =-30V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		17.4		pF	
Reverse Transfer Capacitance	C _{rss}		9.6		pF	
SWITCHING ^{(2) (3)}						
Turn-On Delay Time	t _{d(on)}		1.6		ns	V _{DD} =-30V, I _D =-1A R _G 6.0Ω, V _{GS} =-10V
Rise Time	t _r		2.3		ns	
Turn-Off Delay Time	t _{d(off)}		13		ns	
Fall Time	t _f		5.8		ns	
Gate Charge	Q _g		2.4		nC	V _{DS} =-30V,V _{GS} =-5V, I _D =-0.9A
Total Gate Charge	Q _g		5.1		nC	V _{DS} =-30V,V _{GS} =-10V, I _D =-0.9A
Gate-Source Charge	Q _{gs}		0.7		nC	
Gate-Drain Charge	Q _{gd}		0.7		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage ⁽¹⁾	V _{SD}		-0.85	-0.95	V	T _J =25°C, I _S =-0.8A, V _{GS} =0V
Reverse Recovery Time ⁽³⁾	t _{rr}		22.6		ns	T _J =25°C, I _F =-0.9A, di/dt= 100A/μs
Reverse Recovery Charge ⁽³⁾	Q _{rr}		23.2		nC	

NOTES:

- (1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.
(2) Switching characteristics are independent of operating junction temperature.
(3) For design aid only, not subject to production testing.

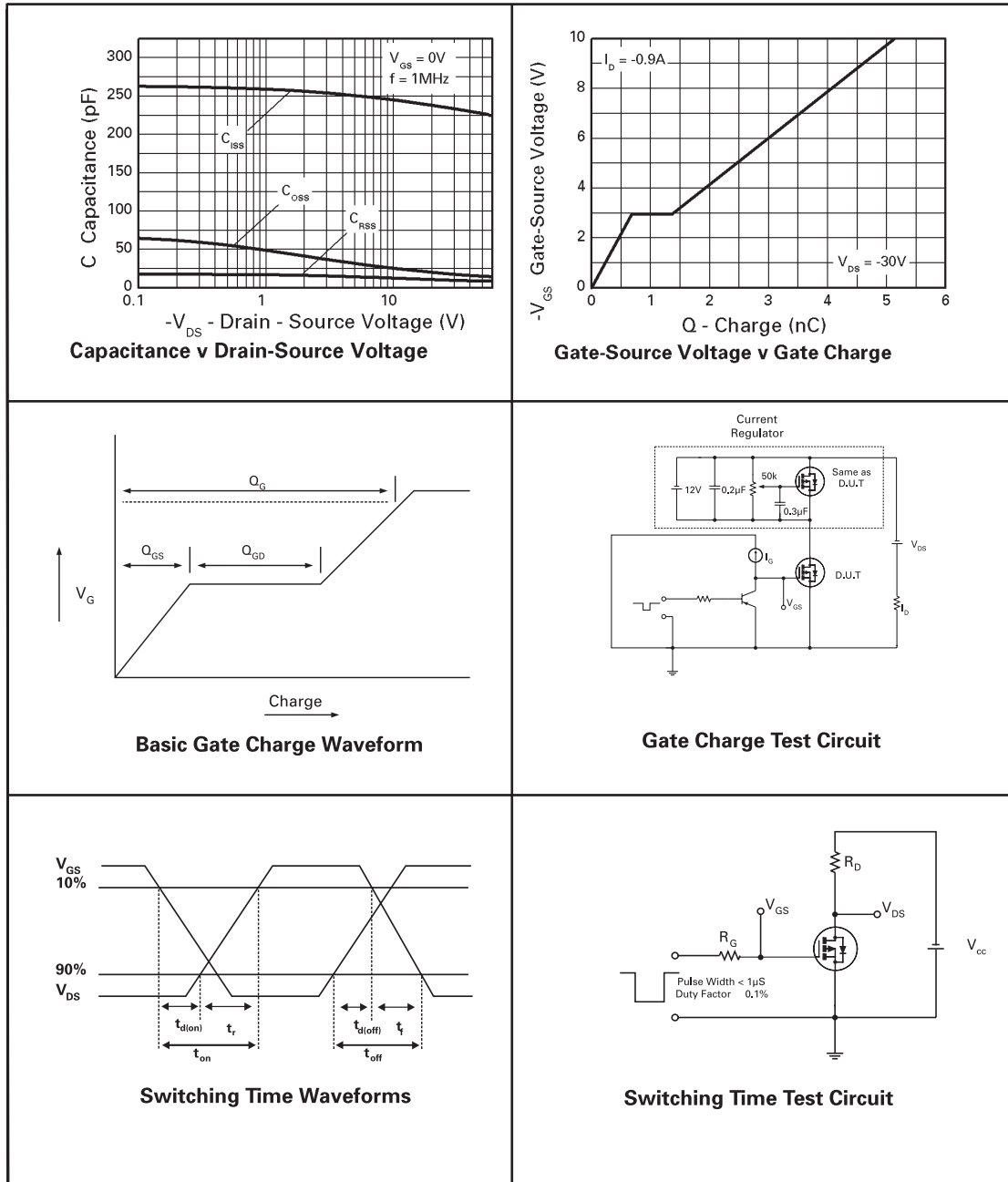
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TYPICAL CHARACTERISTICS



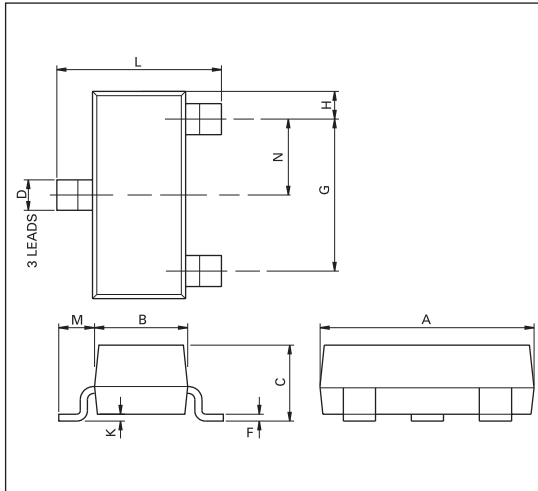
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TYPICAL CHARACTERISTICS

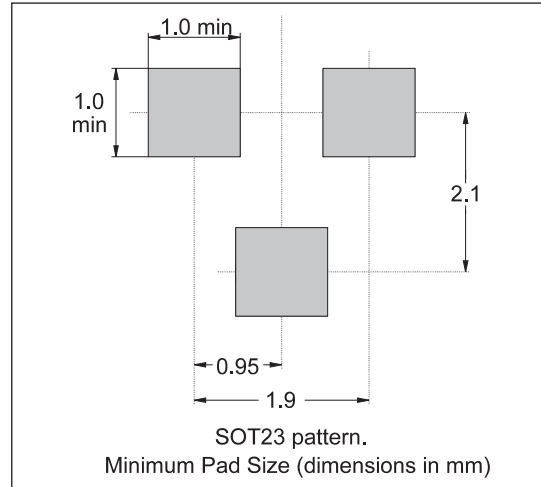


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PACKAGE OUTLINE



PAD LAYOUT



PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Max	Max
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	—	1.10	—	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		—	—		—	

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